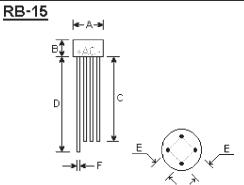
RB151 THRU RB157

SINGLE-PHASE SILICON BRIDGE Reverse Voltage - 50 to 1000 Volts Forward Current - 1.5 Amperes

Features

- Surge overload rating 50 amperes peak
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Mounting Position: Any

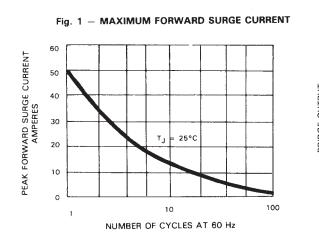


DIMENSIONS									
DIM	inches		m	Note					
	Min.	Max.	Min.	Max.	Note				
А	0.340	0.360	8.6	9.1	ф				
В	0.130	0.150	3.3	3.8					
С	1.20	-	30.5	-					
D	1.27	-	32.3	-					
E	0.180	0.220	4.6	5.6					
F	0.028	0.032	0.71	0.81	ф				

Maximum Ratings and Electrical Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

	Symbols	RB151	RB152	RB153	RB154	RB155	RB156	RB157	Units
Maximum repetitive peak reverse voltage	V _{RRM}	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V _{RMS}	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V _{DC}	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current $T_{A}\text{=}25^\circ\mathrm{C}$	I _(AV)	1.5							Amps
Peak forward surge current, 8.3mS single half sine-wave superimposed on rated load	I FSM	50.0							Amps
1 ² t Rating for fusing (t<8.35ms)	l²t	5.0							A ² t
Maximum forward voltage drop per element at 1.0A peak	V _F	1.0							Volt
$\begin{array}{ll} \mbox{Maximum DC reverse current at rated} & T_{\rm A} = 25 \ensuremath{^{\circ}\rm C}\ & T_{\rm A} = 100 \ensuremath{^{\circ}\rm C}\ & T_{\rm $	I _R	10.0 1.0							μA mA
Operating temperature range	T	-55 to +125							°C
Storage temperature range	T _{stg}	-55 to +150							°C



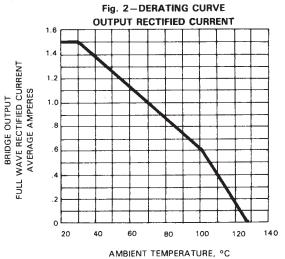


Fig. 3 – TYPICAL FORWARD CHARACTERISTICS

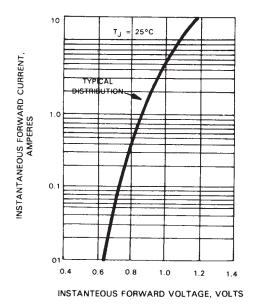
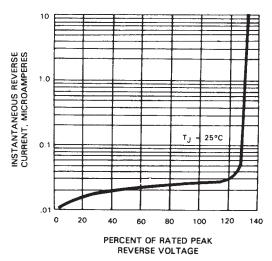


Fig. 4 – TYPICAL REVERSE CHARACTERISTICS



RATINGS AND CHARACTERISTIC CURVES